

## Supporting Information

### Understanding Charge Transport in Endohedral Fullerene Single-Crystal Field-Effect Transistors

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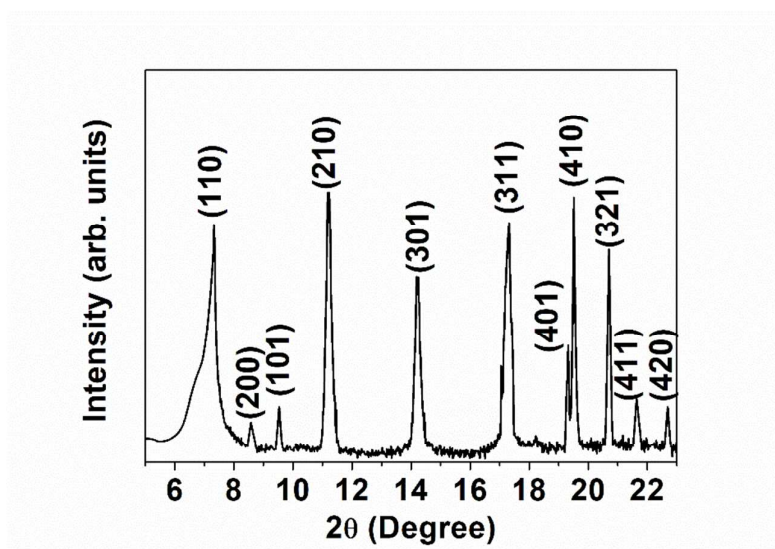
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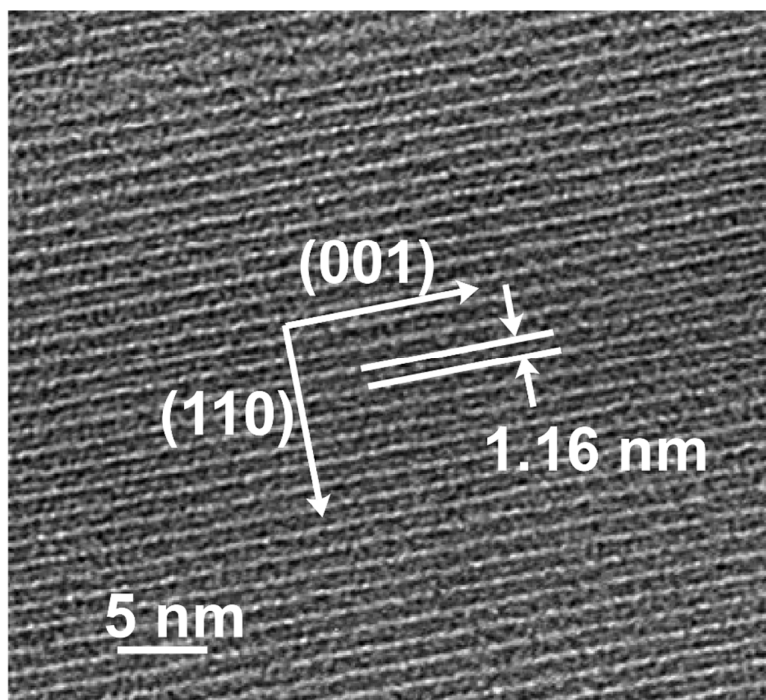
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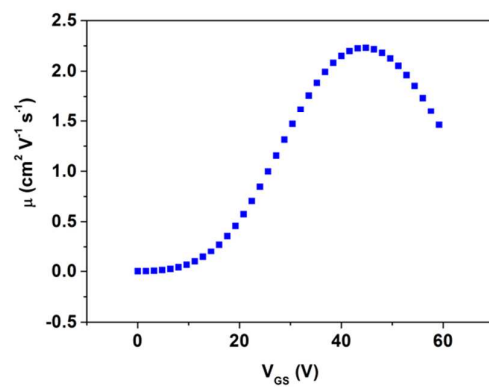
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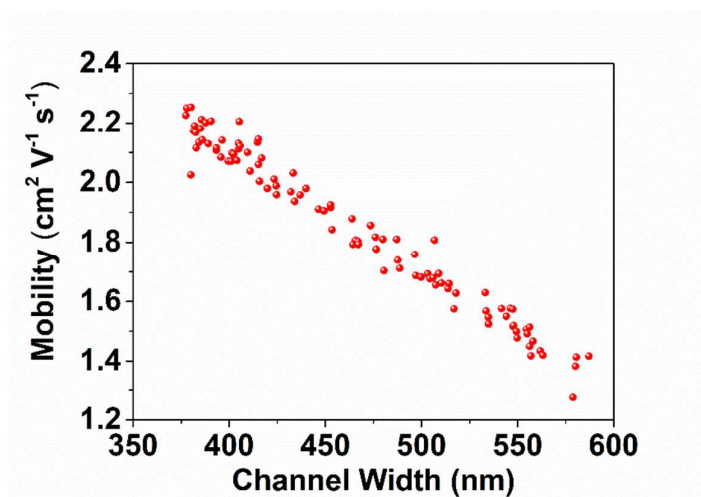
**Figure S1** XRD pattern of as-prepared N@C<sub>60</sub> single crystals.



**Figure S2** HRTEM image of as-prepared N@C<sub>60</sub> single crystal.



**Figure S3** Typical gate-bias dependent mobility for devices based on N@C<sub>60</sub> needle crystals.



**Figure S4** Channel width dependences of mobilities in OFETs based on N@C<sub>60</sub> single crystals.